Abstracts

Improvements on a GaAs MESFET model for nonlinear RF simulations

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F. Ellinger, J. Kucera and W. Baechtold. "Improvements on a GaAs MESFET model for nonlinear RF simulations." 1998 MTT-S International Microwave Symposium Digest 98.3 (1998 Vol. III [MWSYM]): 1623-1626.

A modified GaAs MESFET-model has been developed to improve accuracy over a large bias range, particularly within the linear region. The enhancements consist of a modified Statz equation for the gate charge to improve the modeling of the gate drain capacitance, and an equation for the bias dependent drain source resistance for exact modeling of the dispersive output conductance.

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